

**160V PNP SMALL SIGNAL TRANSISTOR IN SOT323**
**Features**

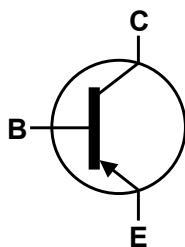
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMST5551
- Ideal for Low Power Amplification and Switching
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

**Mechanical Data**

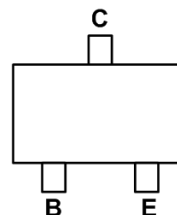
- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.006 grams (approximate)



Top View



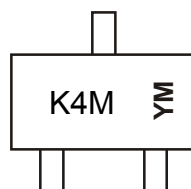
Device Symbol


 Top View  
Pin-Out

**Ordering Information** (Notes 4 & 5)

Device	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per reel
MMST5401-7-F	AEC-Q101	K4M	7	8	3,000
MMST5401-13-F	AEC-Q101	K4M	13	8	10,000
MMST5401Q-7-F	Automotive	K4M	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_compliance\\_definitions/](http://www.diodes.com/quality/product_compliance_definitions/).
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**


K4M = Product Type Marking Code  
 YM = Date Code Marking  
 Y or Y = Year (ex: A = 2013)  
 M or M = Month (ex: 9 = September)

## Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-160	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-150	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Continuous Collector Current	I <sub>C</sub>	-200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 8)					
Collector-Base Breakdown Voltage	V <sub>CBO</sub>	-160	—	V	I <sub>C</sub> = -100μA, I <sub>E</sub> = 0
Collector-Emitter Breakdown Voltage	V <sub>CEO</sub>	-150	—	V	I <sub>C</sub> = -1.0mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	V <sub>EBO</sub>	-5.0	—	V	I <sub>E</sub> = -10μA, I <sub>C</sub> = 0
Collector Cutoff Current	I <sub>CBO</sub>	—	-50	nA μA	V <sub>CB</sub> = -120V, I <sub>E</sub> = 0 V <sub>CB</sub> = -120V, I <sub>E</sub> = 0, T <sub>A</sub> = +100°C
Emitter Cutoff Current	I <sub>EBO</sub>	—	-50	nA	V <sub>EB</sub> = -3.0V, I <sub>C</sub> = 0
<b>ON CHARACTERISTICS</b> (Note 8)					
DC Current Gain	h <sub>FE</sub>	50 60 50	— 240 —	—	I <sub>C</sub> = -1.0mA, V <sub>CE</sub> = -5.0V I <sub>C</sub> = -10mA, V <sub>CE</sub> = -5.0V I <sub>C</sub> = -50mA, V <sub>CE</sub> = -5.0V
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-0.2 -0.5	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	-1.0	V	I <sub>C</sub> = -10mA, I <sub>B</sub> = -1.0mA I <sub>C</sub> = -50mA, I <sub>B</sub> = -5.0mA
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	C <sub>obo</sub>	—	6.0	pF	V <sub>CB</sub> = -10V, f = 1.0MHz, I <sub>E</sub> = 0
Small Signal Current Gain	h <sub>fe</sub>	40	200	—	V <sub>CE</sub> = -10V, I <sub>C</sub> = -1.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f <sub>T</sub>	100	300	MHz	V <sub>CE</sub> = -10V, I <sub>C</sub> = -10mA, f = 100MHz
Noise Figure	NF	—	8.0	dB	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -200μA, R <sub>S</sub> = 10Ω, f = 1.0kHz

- Notes:
6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
  8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

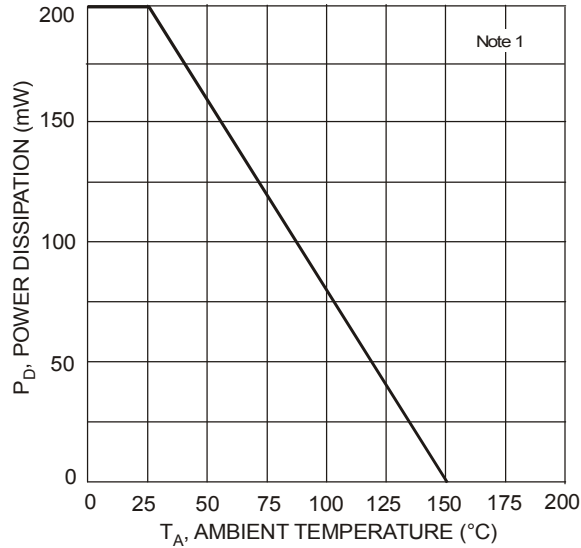


Fig. 1, Max Power Dissipation vs. Ambient Temperature

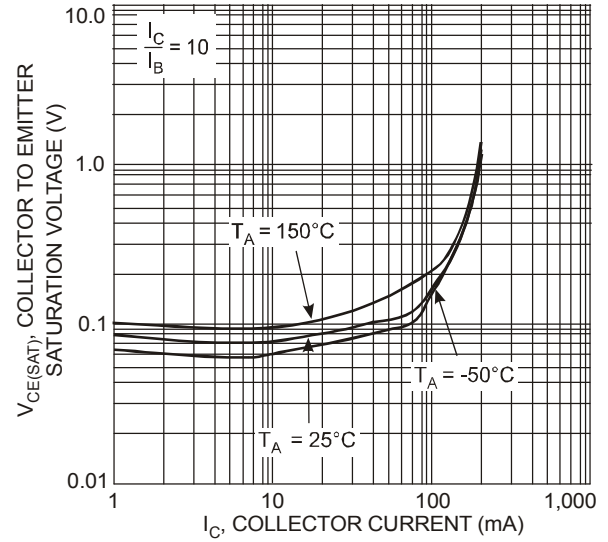


Fig. 2, Collector Emitter Saturation Voltage vs. Collector Current

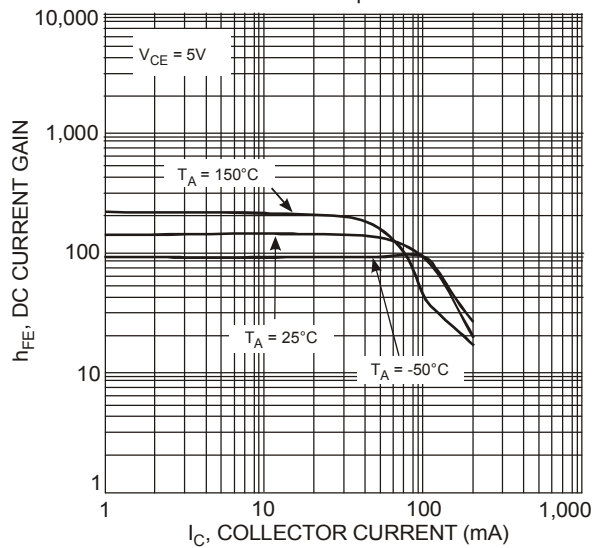


Fig. 3, DC Current Gain vs. Collector Current

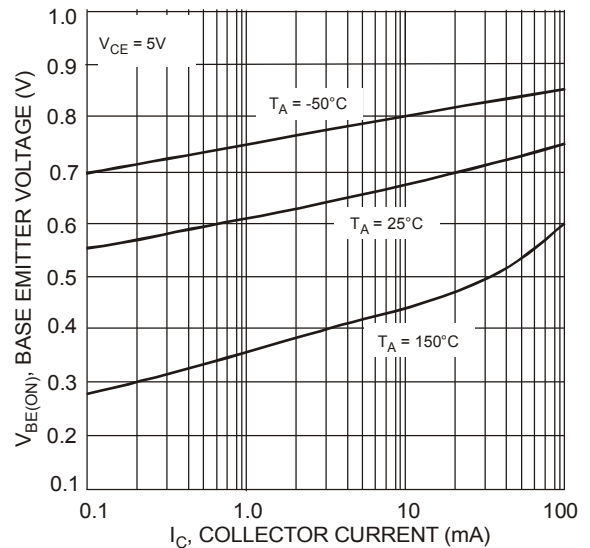


Fig. 4, Base Emitter Voltage vs. Collector Current

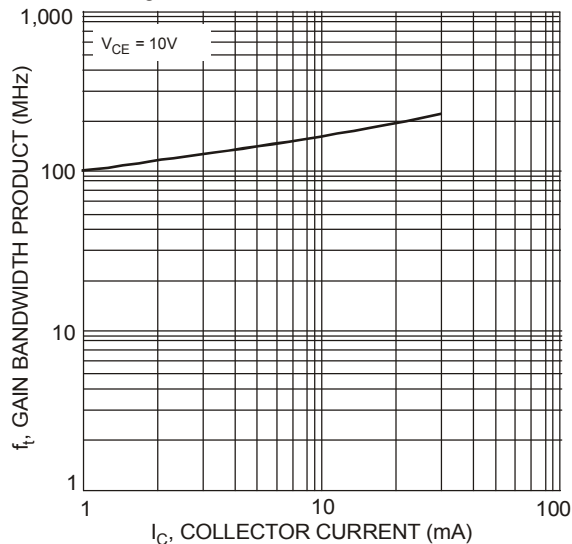
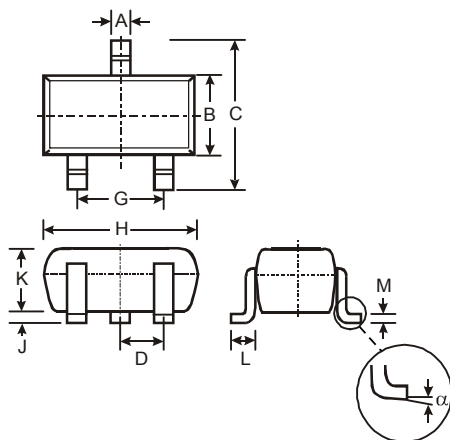


Fig. 5, Gain Bandwidth Product vs. Collector Current

## Package Outline Dimensions

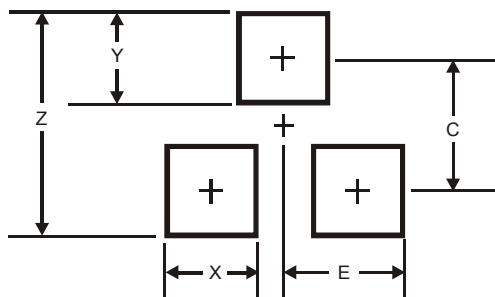
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
$\alpha$	0°	8°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.

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